# N-Channel 30-V (D-S) MOSFET

### **Key Features:**

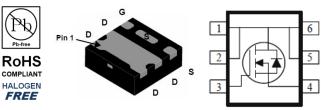
- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- Fast switching speed

## **Typical Applications:**

- Power Routing
- Li Ion Battery Packs
- Level Shifting and Driver Circuits

PRODUCT SUMMARY				
Vds (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)		
30	27 @ V <sub>GS</sub> = 4.5V	7.3		
30	38 @ V <sub>GS</sub> = 2.5V	6.1		

### DFN1.6x1.6-6L



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Limit	Units				
Drain-Source Voltage			30	V			
Gate-Source Voltage	V <sub>GS</sub>	±12	V				
	T <sub>A</sub> =25°C	I	7.3				
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =70°C	I <sub>D</sub>	4.2	А			
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	25				
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	1.9	А				
Dever Dissinction <sup>a</sup>	T <sub>A</sub> =25°C	P <sub>D</sub>	2.1	W			
Power Dissipation <sup>a</sup>	T <sub>A</sub> =70°C	' D	0.7	vv			
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C			

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	$R_{\thetaJA}$	70	°C/W			
	Steady State	INθJA	100	C/VV			

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

# **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit		
Static								
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	0.4			V		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 12 V$			±100	nA		
Zero Gate Voltage Drain Current		$V_{DS} = 24 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			1 uA			
	IDSS	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	uA		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	10			А		
Drain-Source On-Resistance <sup>a</sup>	r.	$V_{GS} = 4.5 \text{ V}, I_{D} = 5 \text{ A}$	27		27	mΩ		
Drain-Source On-Resistance	r <sub>DS(on)</sub>	$V_{GS} = 2.5 \text{ V}, I_{D} = 4 \text{ A}$			38	11122		
Forward Transconductance <sup>a</sup>	<b>g</b> <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 5 \text{ A}$		20		S		
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = 0.9 \text{ A}, V_{GS} = 0 \text{ V}$		0.71		V		
		Dynamic <sup>b</sup>						
Total Gate Charge	Qg	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$		7				
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 13 V, V_{GS} = 4.5 V,$ $I_{D} = 4 A$		0.9		nC		
Gate-Drain Charge	$Q_gd$	10		2.2				
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = 15 \text{ V}, \text{ R}_{L} = 3.8 \Omega,$		8				
Rise Time	t <sub>r</sub>	$V_{\rm DS} = 13$ V, $N_{\rm L} = 3.0$ 22, $I_{\rm D} = 4$ A,		17		ns		
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{\text{GEN}} = 4.5 \text{ V}, \text{ R}_{\text{GEN}} = 6 \Omega$		44				
Fall Time	t <sub>f</sub>	$V_{\text{GEN}} = 4.5 \text{ V}, \text{ (C}_{\text{EN}} = 0.22 $		11				
Input Capacitance	C <sub>iss</sub>			561				
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		55		pF		
Reverse Transfer Capacitance	C <sub>rss</sub>			45				

### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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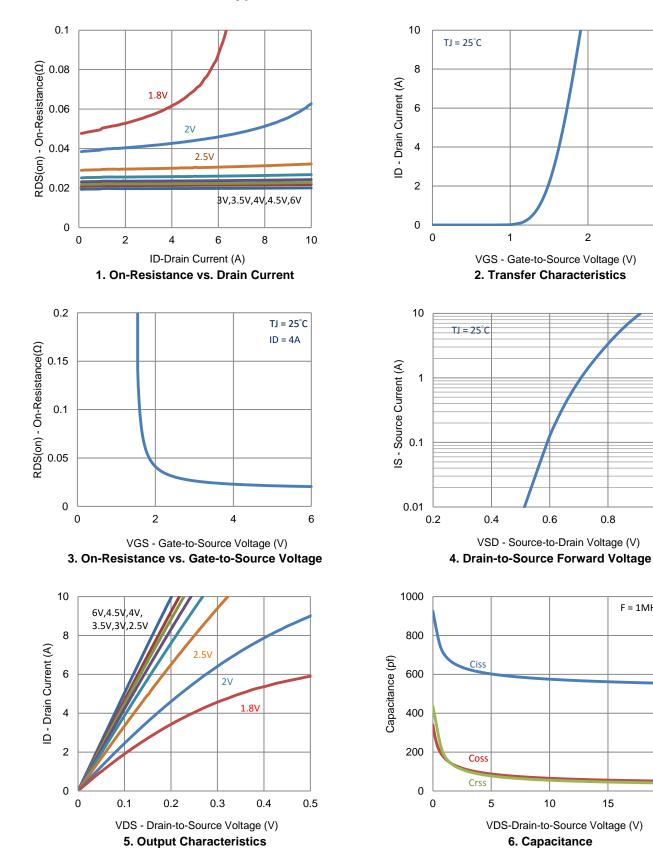
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20

F = 1MHz

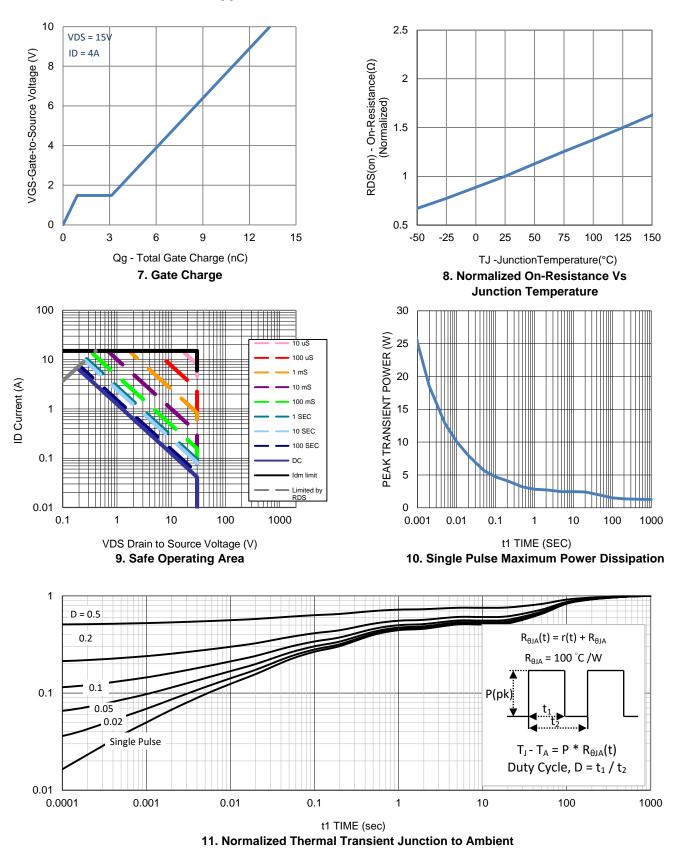
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0.8



# **Typical Electrical Characteristics**

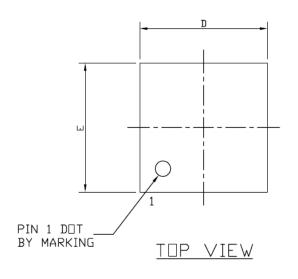
15

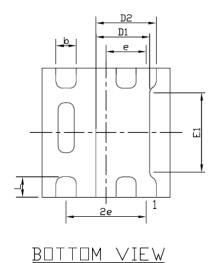


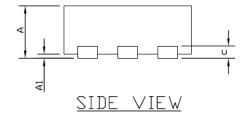
# **Typical Electrical Characteristics**

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SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
	MIN	NDM	MAX	MIN	NDM	MAX	
A	0.50	0.55	0.60	0.020	0.022	0.024	
A1	0.00		0.05	0.000		0.002	
b	0.22	0.25	0.28	0.009	0.010	0.011	
С	0.152 Ref.			0.006 Ref.			
D	1.55	1.60	1.65	0.061	0.063	0.065	
D1	0.67 TYP			0.026 TYP			
D2	0.75 TYP			0.030 TYP			
E	1.55	1.60	1.65	0.061	0.063	0.065	
E1	0.98 TYP				0.039 TYP		
e	0.50 BSC			0.020 BSC			
L	0.20	0.25	0.30	0.008	0.010	0.012	